



# FQD2P25 / FQU2P25

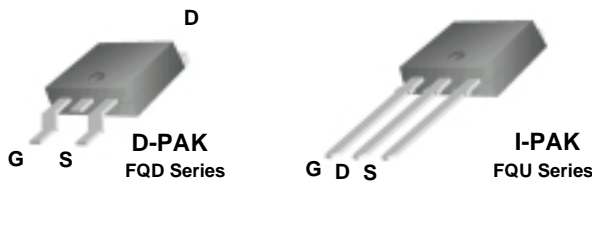
## 250V P-Channel MOSFET

### General Description

These P-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switching DC/DC converters.

### Features

- -2.0A, -250V,  $R_{DS(on)} = 4.0\Omega @ V_{GS} = -10V$
- Low gate charge ( typical 6.5 nC)
- Low Crss ( typical 6.5 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FQD2P25 / FQU2P25	Units
$V_{DSS}$	Drain-Source Voltage	-250	V
$I_D$	Drain Current - Continuous ( $T_C = 25^\circ\text{C}$ )	-2.0	A
	- Continuous ( $T_C = 100^\circ\text{C}$ )	-1.27	A
$I_{DM}$	Drain Current - Pulsed (Note 1)	-8.0	A
$V_{GSS}$	Gate-Source Voltage	$\pm 30$	V
$E_{AS}$	Single Pulsed Avalanche Energy (Note 2)	120	mJ
$I_{AR}$	Avalanche Current (Note 1)	-2.0	A
$E_{AR}$	Repetitive Avalanche Energy (Note 1)	3.7	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	-5.5	V/ns
$P_D$	Power Dissipation ( $T_A = 25^\circ\text{C}$ ) *	2.5	W
	Power Dissipation ( $T_C = 25^\circ\text{C}$ )	37	W
	- Derate above $25^\circ\text{C}$	0.29	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$T_L$	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	3.4	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient *	--	50	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	110	$^\circ\text{C}/\text{W}$

\* When mounted on the minimum pad size recommended (PCB Mount)

## Electrical Characteristics

$T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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### Off Characteristics

$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-250	--	--	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$	--	-0.2	--	$\text{V}/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = -250\text{ V}, V_{GS} = 0\text{ V}$	--	--	-1	$\mu\text{A}$
		$V_{DS} = -200\text{ V}, T_C = 125^\circ\text{C}$	--	--	-10	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage Current, Forward	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA

### On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-3.0	--	-5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = -10\text{ V}, I_D = -1.0\text{ A}$	--	3.15	4.0	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = -40\text{ V}, I_D = -1.0\text{ A}$ (Note 4)	--	1.1	--	S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = -25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	190	250	pF
$C_{oss}$	Output Capacitance		--	40	55	pF
$C_{rss}$	Reverse Transfer Capacitance		--	6.5	8.5	pF

### Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -125\text{ V}, I_D = -2.3\text{ A},$ $R_G = 25\ \Omega$	--	8.5	25	ns	
$t_r$	Turn-On Rise Time		--	40	90	ns	
$t_{d(off)}$	Turn-Off Delay Time		(Note 4, 5)	--	12	35	ns
$t_f$	Turn-Off Fall Time		(Note 4, 5)	--	25	60	ns
$Q_g$	Total Gate Charge	$V_{DS} = -200\text{ V}, I_D = -2.3\text{ A},$ $V_{GS} = -10\text{ V}$	--	6.5	8.5	nC	
$Q_{gs}$	Gate-Source Charge		(Note 4, 5)	--	1.8	--	nC
$Q_{gd}$	Gate-Drain Charge		(Note 4, 5)	--	3.0	--	nC

### Drain-Source Diode Characteristics and Maximum Ratings

$I_S$	Maximum Continuous Drain-Source Diode Forward Current	--	--	-2.0	A	
$I_{SM}$	Maximum Pulsed Drain-Source Diode Forward Current	--	--	-8.0	A	
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = -2.0\text{ A}$	--	--	-5.0	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = -2.3\text{ A},$	--	110	--	ns
$Q_{rr}$	Reverse Recovery Charge	$dI_F / dt = 100\text{ A}/\mu\text{s}$ (Note 4)	--	0.4	--	$\mu\text{C}$

#### Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2.  $L = 48\text{ mH}, I_{AS} = -2.0\text{ A}, V_{DD} = -50\text{ V}, R_G = 25\ \Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq -2.3\text{ A}, dI/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width  $\leq 300\ \mu\text{s}$ , Duty cycle  $\leq 2\%$
5. Essentially independent of operating temperature

## Typical Characteristics

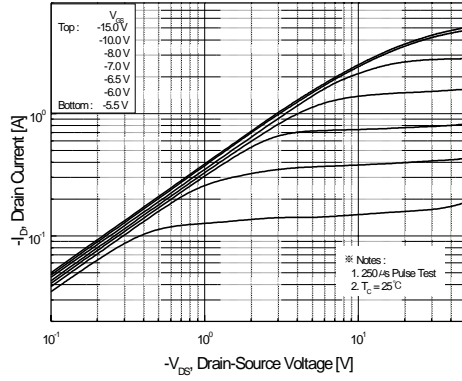


Figure 1. On-Region Characteristics

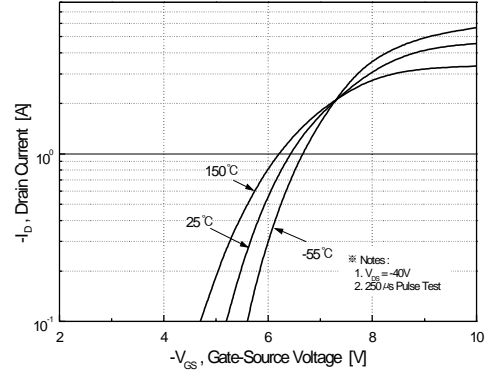


Figure 2. Transfer Characteristics

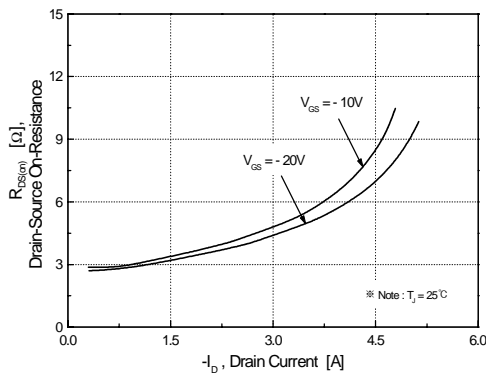


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

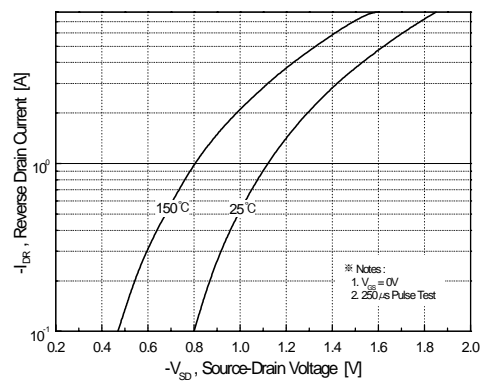


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

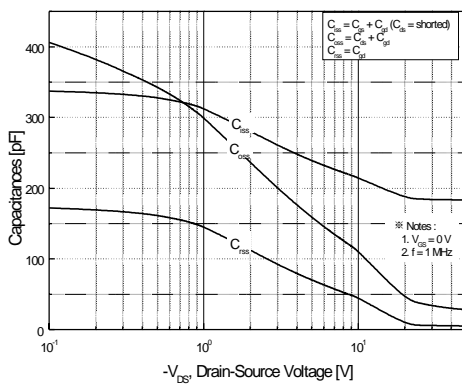


Figure 5. Capacitance Characteristics

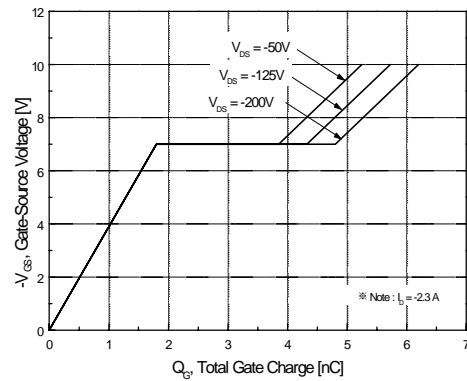


Figure 6. Gate Charge Characteristics